

	Type	L #	Hits	Search Text	DBs
1	BRS	L5	4319	(peripheral or logic) and "floating gate" and "control gate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L6	771	(silicide or salicide) and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L7	658	@ad<=20000525 and 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L8	643	substrate and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	14451	"floating gate" and "control gate"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	1924	(silicide or salicide) and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	1857	semiconductor and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	1790	substrate and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	1184	@ad<=20000525 and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	0	"cyclical deposit\$4"	USPAT
7	BRS	L7	15664	cyclical	USPAT
8	BRS	L8	2067	capacitor and 7	USPAT
9	BRS	L9	37	deposit\$4 near5 cyclical	USPAT
10	BRS	L10	2	capacitor and 9	USPAT
11	BRS	L11	0	tungsten near7 9	USPAT
12	BRS	L12	0	(deposit\$4 near5 cyclical) near10 tungsten	USPAT